N-Channel Enhancement Mode Power MOSFET

MTN10N40E3

BV_{DSS} : 400V
$R_{DS(ON)}$: 0.47Ω (typ.)
I_D : 10A

Description

The MTN10N40E3 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness.
The TO-220 package is universally preferred for all commercial-industrial applications

Features

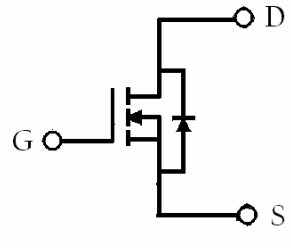
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

Applications

- Switching Mode Power Supply

Symbol

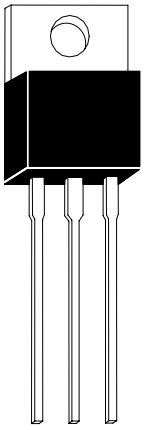
MTN10N40E3



G：Gate
D：Drain
S：Source

Outline

TO-220



G D S

Absolute Maximum Ratings (T_C=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage (Note 1)	V_{DS}	400	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current	I_D	10*	A
Continuous Drain Current @T_C=100°C	I_D	6*	A
Pulsed Drain Current @ V_{GS}=10V (Note 2)	I_{DM}	40*	A
Single Pulse Avalanche Energy (Note 3)	E_{AS}	457	mJ
Avalanche Current (Note 2)	I_{AR}	10	A
Repetitive Avalanche Energy (Note 2)	E_{AR}	12.5	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Maximum Temperature for Soldering @ Lead at 0.125in(3.175mm) from case for 10 seconds	T_L	300	°C
Total Power Dissipation (T_C=25℃)	P_D	125	W
Linear Derating Factor above 25℃		1	W/°C
Operating Junction and Storage Temperature	Tj, Tstg	-55~+150	°C

*Drain current limited by maximum junction temperature

Note : 1. T_J=+25℃ to +150℃.
2. Repetitive rating; pulse width limited by maximum junction temperature.
3. I_{SD}=10A, dI/dt<100A/μs, V_{DD}<BV_{DSS}, T_J=+150℃.
4. I_{AS}=10A, V_{DD}=50V, L=8mH, R_G=25Ω, starting T_J=+25℃.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	1	°C/W
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	62.5	°C/W

Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	400	-	-	V	V_{GS}=0, I_D=250μA
$\Delta BV_{DSS}/\Delta Tj$	-	0.4	-	V/°C	Reference to 25°C, I_D=250μA
$V_{GS(th)}$	2.0	-	4.0	V	V_{DS} = V_{GS}, I_D=250μA
*G_{FS}	-	7	-	S	V_{DS} =15V, I_D=5A
I_{GSS}	-	-	±100	nA	V_{GS}=±30
I_{DSS}	-	-	1	μA	V_{DS} =400V, V_{GS} =0
	-	-	25		V_{DS} =320V, V_{GS} =0, Tj=125°C
*$R_{DS(ON)}$	-	0.47	0.55	Ω	V_{GS} =10V, I_D=6A
Dynamic					
*Qg	-	32	-	nC	I_D=10A, V_{DD}=320V, V_{GS}=10V
*Qgs	-	9	-		
*Qgd	-	12	-		
*$t_{d(ON)}$	-	14	-	ns	V_{DD}=200V, I_D=10A, V_{GS}=10V, R_G=9.1Ω
*tr	-	30	-		
*$t_{d(OFF)}$	-	31	-		
*t_f	-	26	-		
Ciss	-	1400	-	pF	V_{GS}=0V, V_{DS}=25V, f=1MHz
Coss	-	117	-		
Crss	-	25	-		
Source-Drain Diode					
*I_S	-	-	10	A	
*I_{SM}	-	-	40		
*V_{SD}	-	-	1.5	V	I_S=10A, V_{GS}=0V
*trr	-	360	-	ns	V_{GS}=0, I_F=10A, dI/dt=100A/μs
*Qrr	-	3.2	-	μC	

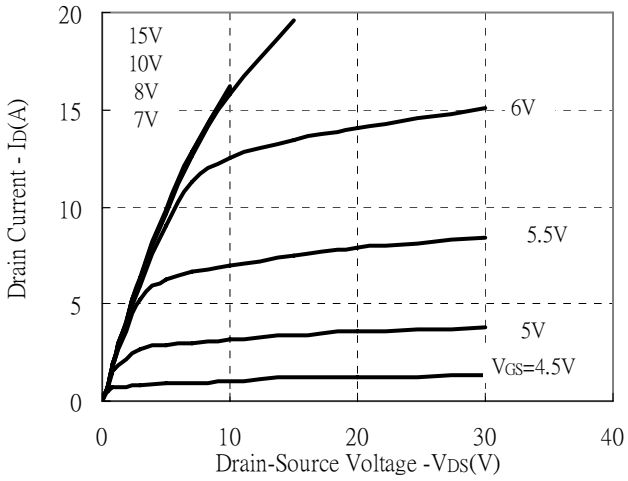
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Ordering Information

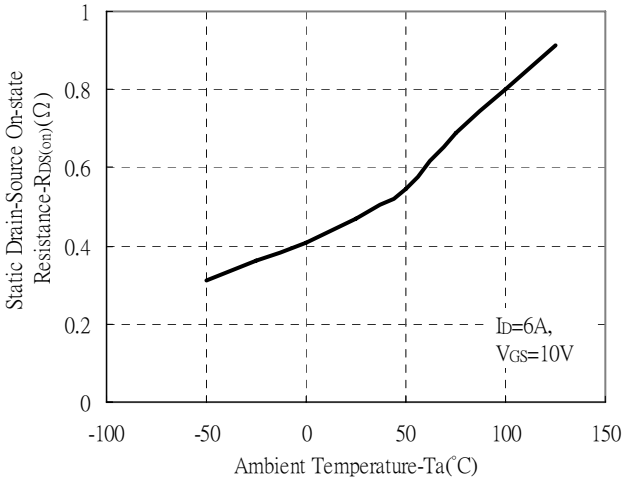
Device	Package	Shipping	Marking
MTN10N40E3	TO-220 (RoHS compliant)	50 pcs/tube, 20 tubes/box, 4 boxes / carton	10N40

Typical Characteristics

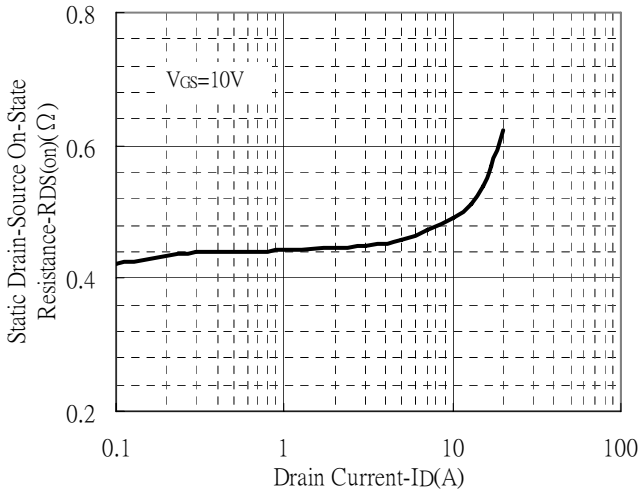
Typical Output Characteristics



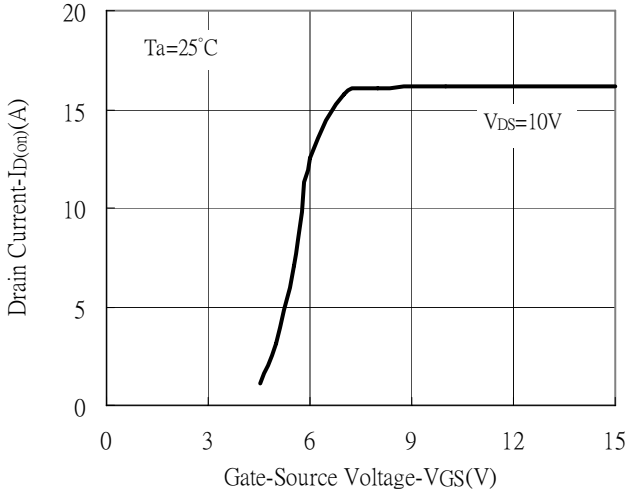
Static Drain-Source On-resistance vs Ambient Temperature



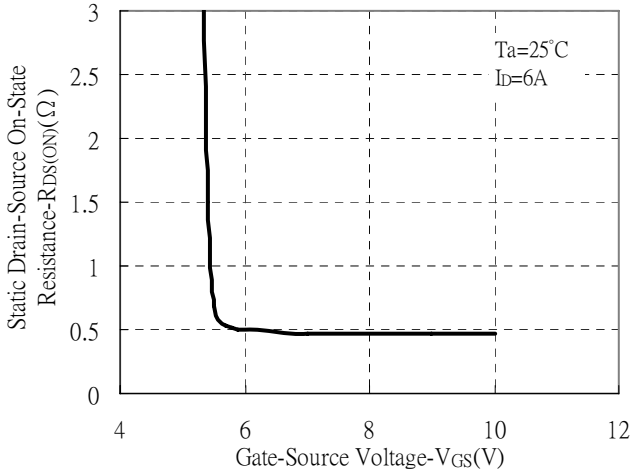
Static Drain-Source On-State resistance vs Drain Current



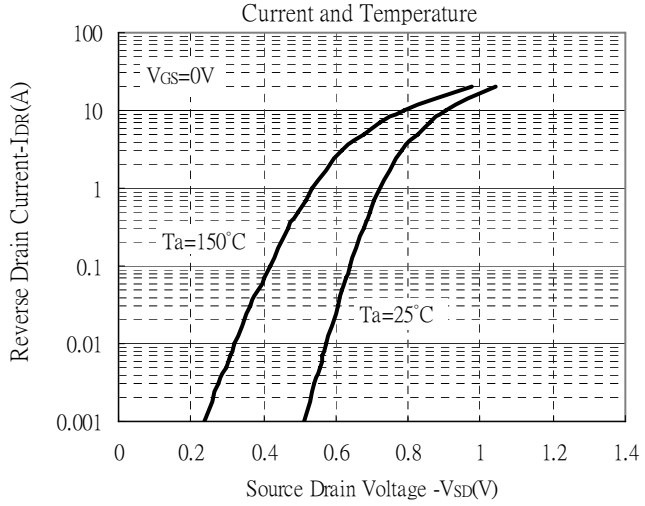
Drain Current vs Gate-Source Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

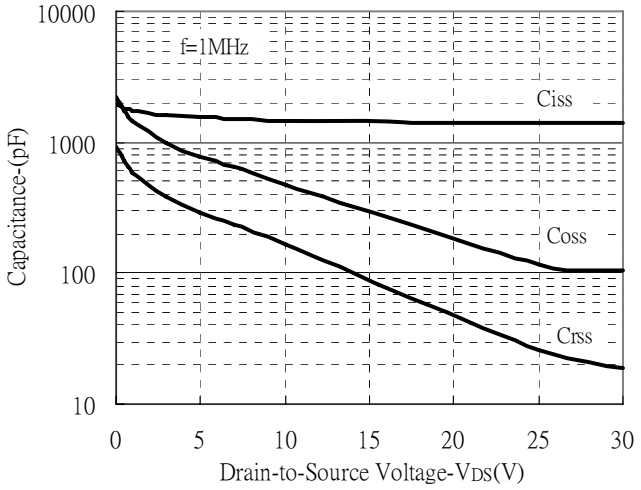


Body Diode Forward Voltage Variation vs Source Current and Temperature

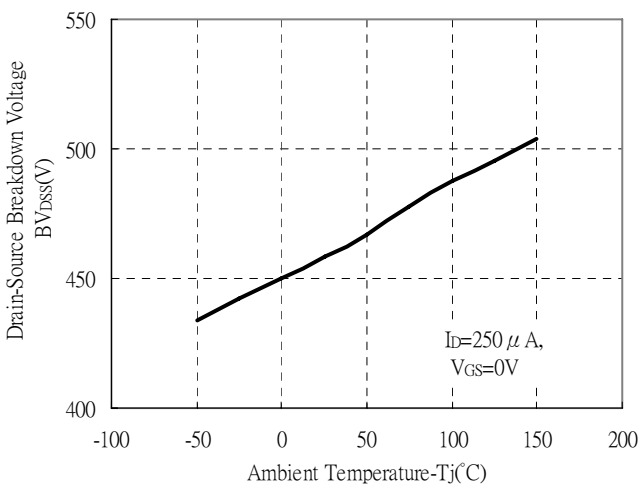


Typical Characteristics(Cont.)

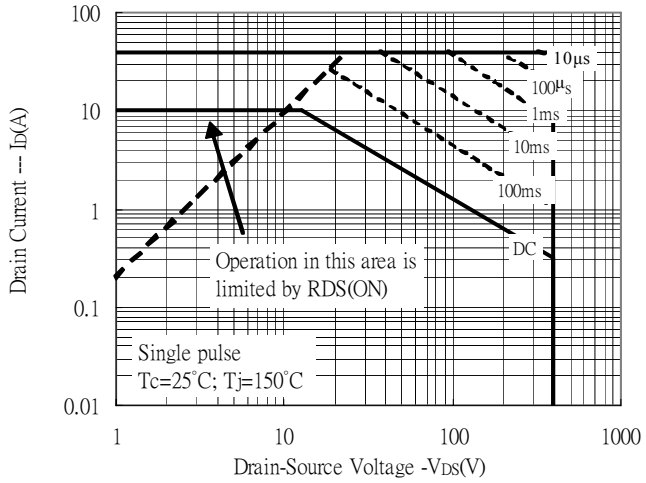
Capacitance vs Reverse Voltage



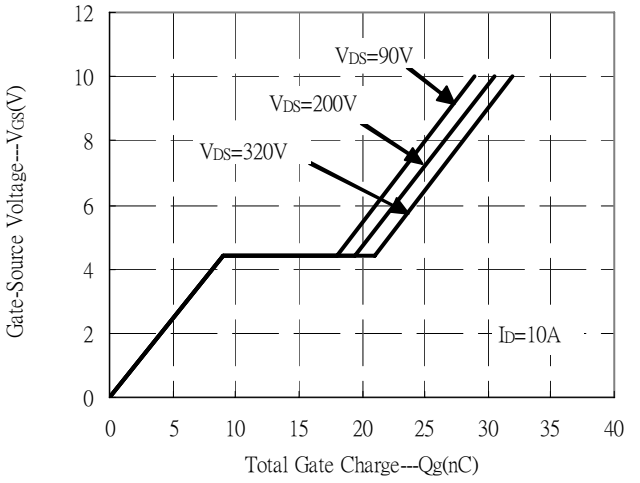
Brekdown Voltage vs Ambient Temperature



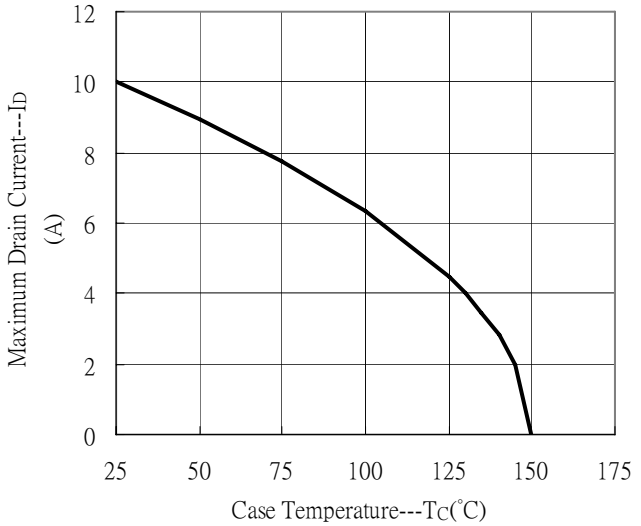
Maximum Safe Operating Area



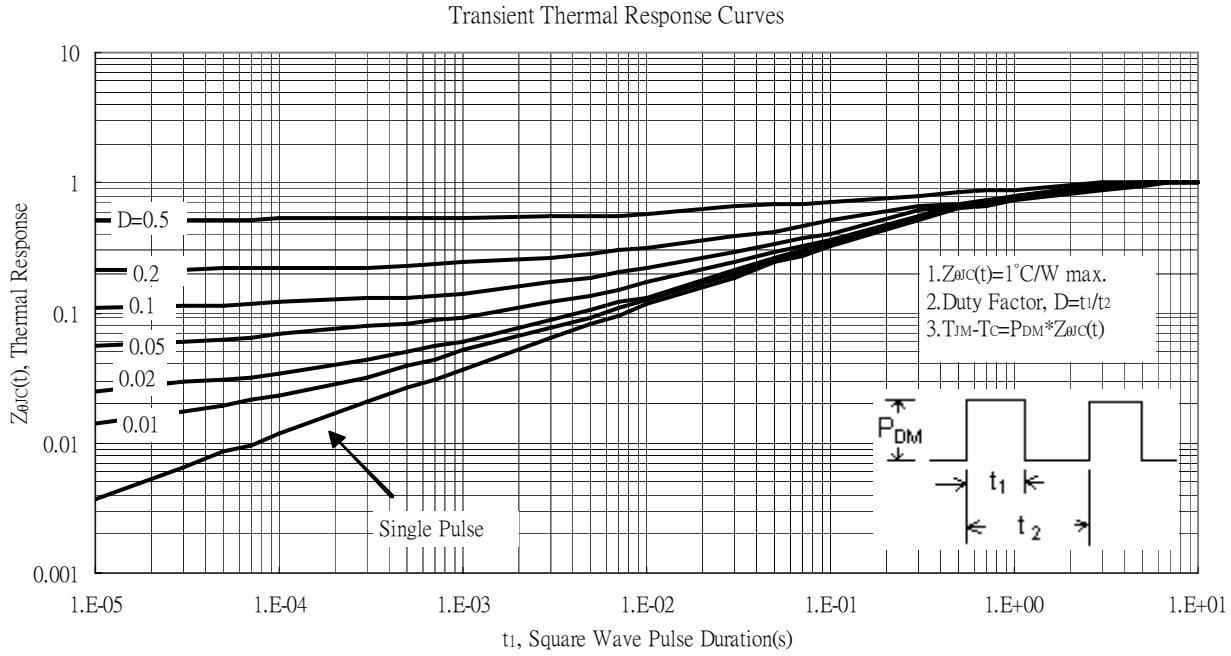
Gate Charge Characteristics



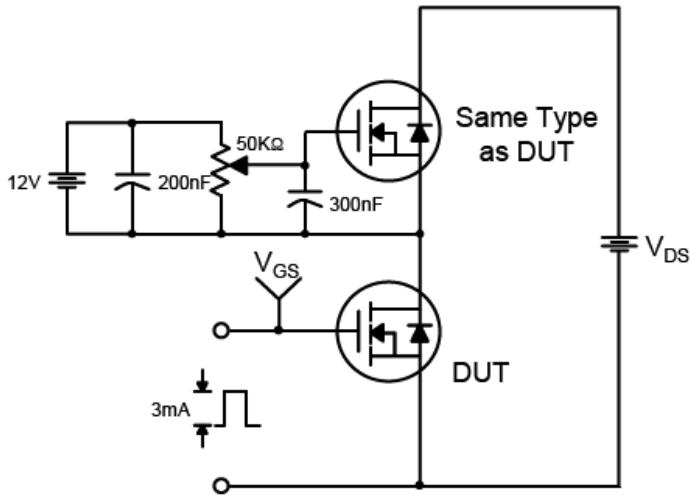
Maximum Drain Current vs Case Temperature

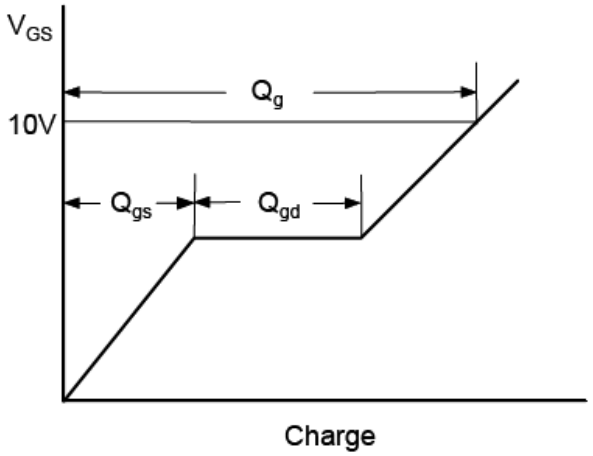


Typical Characteristics(Cont.)

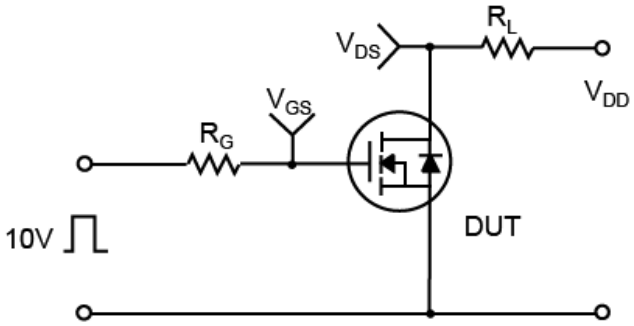


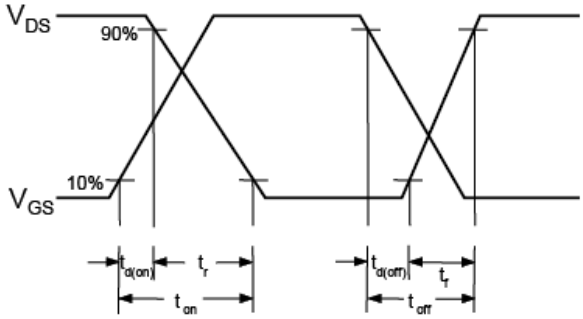
Test Circuit and Waveforms



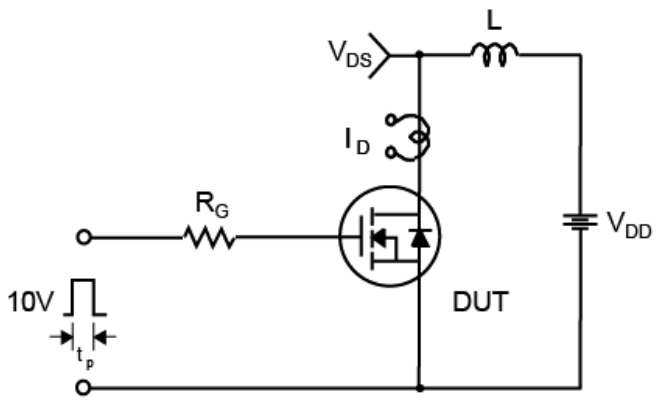


Resistive Switching Test Circuit & Waveforms

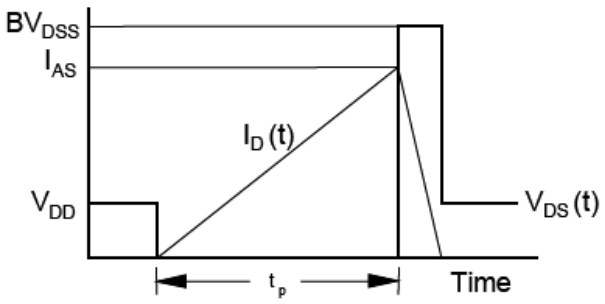




Unclamped Inductive Switching Test Circuit & Waveforms

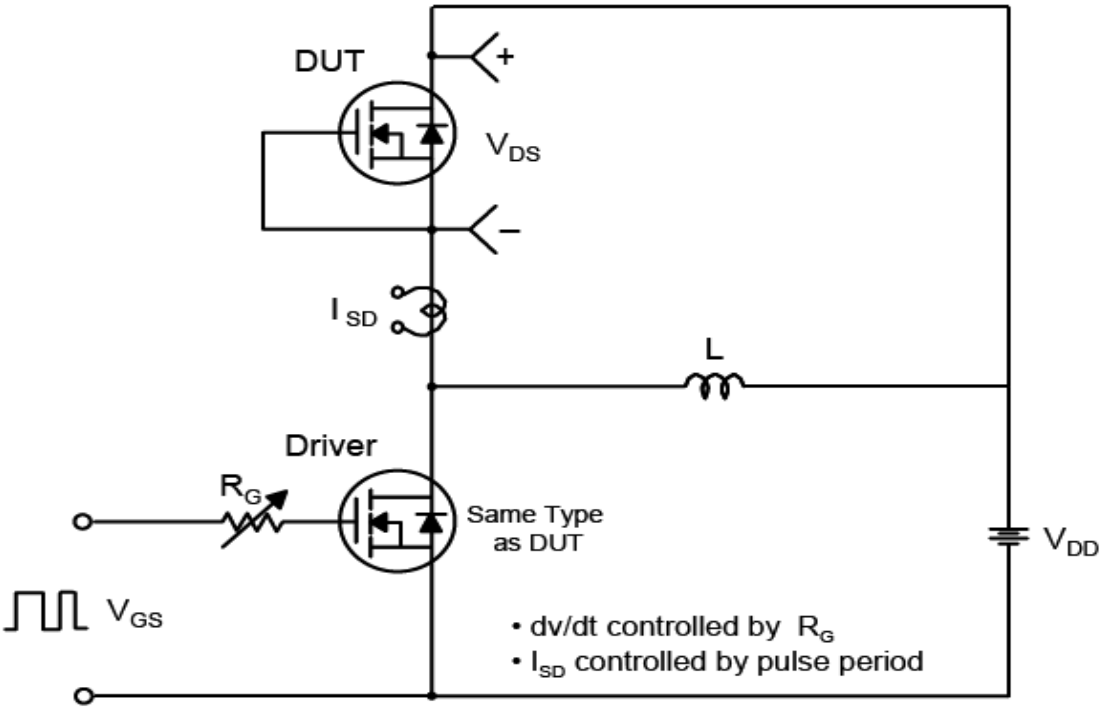


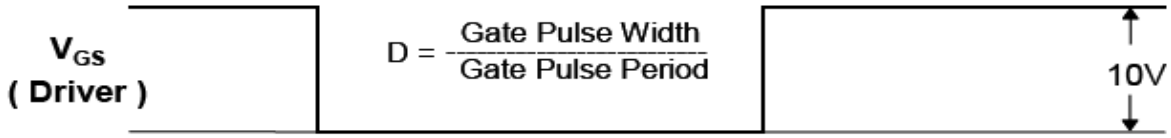
$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

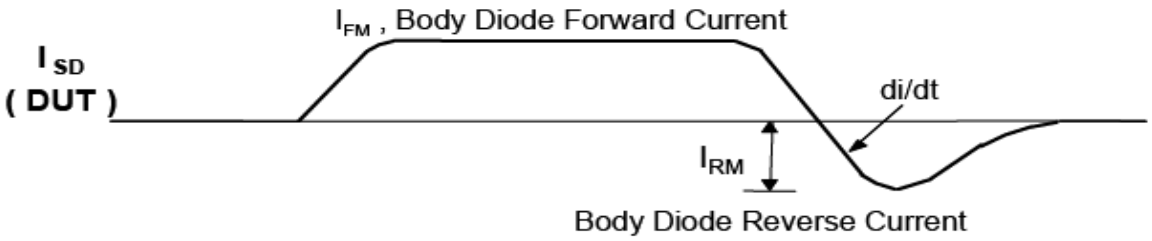


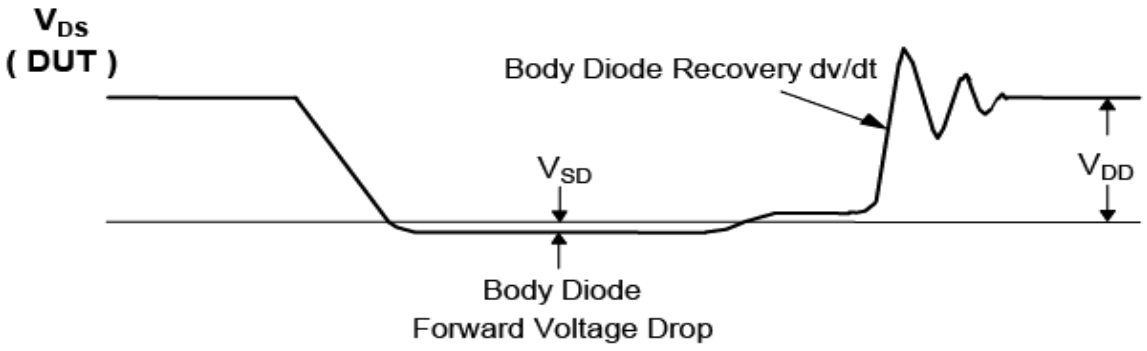
Test Circuit and Waveforms(Cont.)

Peak Diode Recovery dv/dt Test Circuit & Waveforms

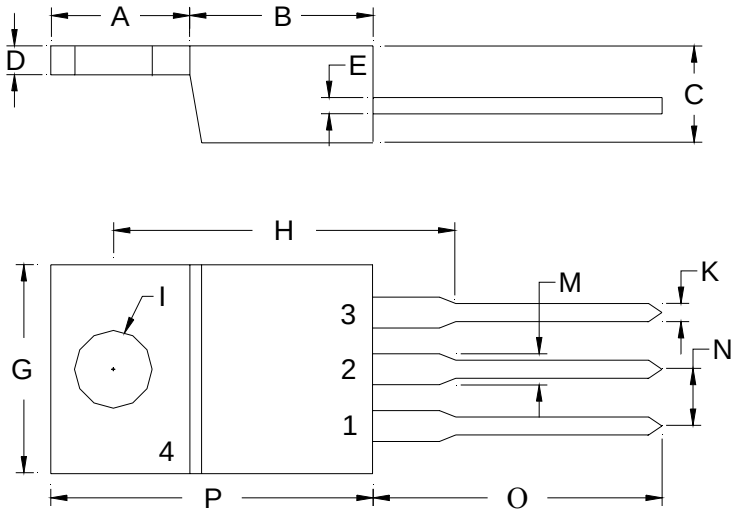






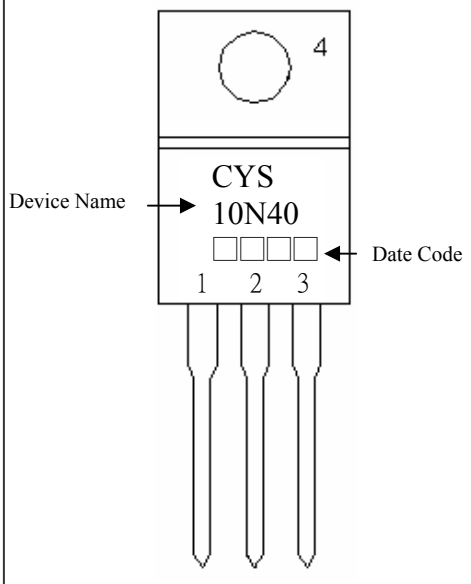


TO-220 Dimension



3-Lead TO-220 Plastic Package
CYStek Package Code: E3

Marking:



Style: Pin 1.Gate 2.Drain 3.Source
4.Drain

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.2441	0.2598	6.20	6.60	I	-	*0.1508	-	*3.83
B	0.3386	0.3543	8.60	9.00	K	0.0299	0.0394	0.76	1.00
C	0.1732	0.1890	4.40	4.80	M	0.0461	0.0579	1.17	1.47
D	0.0492	0.0571	1.25	1.45	N	-	*0.1000	-	*2.54
E	0.0142	0.0197	0.36	0.50	O	0.5217	0.5610	13.25	14.25
G	0.3858	0.4094	9.80	10.40	P	0.5787	0.6024	14.70	15.30
H	-	*0.6398	-	*16.25					

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: KFC ; pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0